



Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101lgafb-30

Table 1-1. List of Ordering Part Numbers

(4/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
44 pins	44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)	Mounted	A	R5F100FAAFP#V0, R5F100FCAFP#V0, R5F100FDAFP#V0, R5F100FEAFP#V0, R5F100FFAFP#V0, R5F100FGAFP#V0, R5F100FHAFP#V0, R5F100FJAFP#V0, R5F100FKAFP#V0, R5F100FLAFP#V0 R5F100FAAFP#X0, R5F100FCAFP#X0, R5F100FDAFP#X0, R5F100FEAFP#X0, R5F100FFAFP#X0, R5F100FGAFP#X0, R5F100FHAFP#X0, R5F100FJAFP#X0, R5F100FKAFP#X0, R5F100FLAFP#X0
			D	R5F100FADFP#V0, R5F100FCDFP#V0, R5F100FDDFP#V0, R5F100FEDFP#V0, R5F100FFDFP#V0, R5F100FGDFP#V0, R5F100FHDFP#V0, R5F100FJDFP#V0, R5F100FKDFP#V0, R5F100FLDFP#V0 R5F100FADFP#X0, R5F100FCDFP#X0, R5F100FDDFP#X0, R5F100FEDFP#X0, R5F100FFDFP#X0, R5F100FGDFP#X0, R5F100FHDFP#X0, R5F100FJDFP#X0, R5F100FKDFP#X0, R5F100FLDFP#X0
			G	R5F100FAGFP#V0, R5F100FCGFP#V0, R5F100FDGFP#V0, R5F100FEGFP#V0, R5F100FFGFP#V0, R5F100FGGFP#V0, R5F100FHGFP#V0, R5F100FJGFP#V0 R5F100FAGFP#X0, R5F100FCGFP#X0, R5F100FDGFP#X0, R5F100FEGFP#X0, R5F100FFGFP#X0, R5F100FGGFP#X0, R5F100FHGFP#X0, R5F100FJGFP#X0
		Not mounted	A	R5F101FAAFP#V0, R5F101FCAFP#V0, R5F101FDAFP#V0, R5F101FEAFP#V0, R5F101FFAFP#V0, R5F101FGAFP#V0, R5F101FHAFP#V0, R5F101FJAFP#V0, R5F101FKAFP#V0, R5F101FLAFP#V0 R5F101FAAFP#X0, R5F101FCAFP#X0, R5F101FDAFP#X0, R5F101FEAFP#X0, R5F101FFAFP#X0, R5F101FGAFP#X0, R5F101FHAFP#X0, R5F101FJAFP#X0, R5F101FKAFP#X0, R5F101FLAFP#X0
			D	R5F101FADFP#V0, R5F101FCDFP#V0, R5F101FDDFP#V0, R5F101FEDFP#V0, R5F101FFDFP#V0, R5F101FGDFP#V0, R5F101FHDFP#V0, R5F101FJDFP#V0, R5F101FKDFP#V0, R5F101FLDFP#V0 R5F101FADFP#X0, R5F101FCDFP#X0, R5F101FDDFP#X0, R5F101FEDFP#X0, R5F101FFDFP#X0, R5F101FGDFP#X0, R5F101FHDFP#X0, R5F101FJDFP#X0, R5F101FKDFP#X0, R5F101FLDFP#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(6/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
48 pins	48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)	Mounted	A	R5F100GAANA#U0, R5F100GCANA#U0, R5F100GDANA#U0, R5F100GEANA#U0, R5F100GFANA#U0, R5F100GGANA#U0, R5F100GHANA#U0, R5F100GJANA#U0, R5F100GKANA#U0, R5F100GLANA#U0 R5F100GAANA#W0, R5F100GCANA#W0, R5F100GDANA#W0, R5F100GEANA#W0, R5F100GFANA#W0, R5F100GGANA#W0, R5F100GHANA#W0, R5F100GJANA#W0, R5F100GKANA#W0, R5F100GLANA#W0
		Not mounted	D	R5F100GADNA#U0, R5F100GCDNA#U0, R5F100GDDNA#U0, R5F100GEDNA#U0, R5F100GFDNA#U0, R5F100GGDNA#U0, R5F100GHDNA#U0, R5F100GJDNA#U0, R5F100GKDNA#U0, R5F100GLDNA#U0 R5F100GADNA#W0, R5F100GCDNA#W0, R5F100GDDNA#W0, R5F100GEDNA#W0, R5F100GFDNA#W0, R5F100GGDNA#W0, R5F100GHDNA#W0, R5F100GJDNA#W0, R5F100GKDNA#W0, R5F100GLDNA#W0
			G	R5F100GAGNA#U0, R5F100GCGNA#U0, R5F100GDGNA#U0, R5F100GEGNA#U0, R5F100GFGNA#U0, R5F100GGGNA#U0, R5F100GHGNA#U0, R5F100GJGNA#U0 R5F100GAGNA#W0, R5F100GCGNA#W0, R5F100GDGNA#W0, R5F100GEGNA#W0, R5F100GFGNA#W0, R5F100GGGNA#W0, R5F100GHGNA#W0, R5F100GJGNA#W0
			A	R5F101GAANA#U0, R5F101GCANA#U0, R5F101GDANA#U0, R5F101GEANA#U0, R5F101GFANA#U0, R5F101GGANA#U0, R5F101GHANA#U0, R5F101GJANA#U0, R5F101GKANA#U0, R5F101GLANA#U0 R5F101GAANA#W0, R5F101GCANA#W0, R5F101GDANA#W0, R5F101GEANA#W0, R5F101GFANA#W0, R5F101GGANA#W0, R5F101GHANA#W0, R5F101GJANA#W0, R5F101GKANA#W0, R5F101GLANA#W0
			D	R5F101GADNA#U0, R5F101GCDNA#U0, R5F101GDDNA#U0, R5F101GEDNA#U0, R5F101GFDNA#U0, R5F101GGDNA#U0, R5F101GHDNA#U0, R5F101GJDNA#U0, R5F101GKDNA#U0, R5F101GLDNA#U0 R5F101GADNA#W0, R5F101GCDNA#W0, R5F101GDDNA#W0, R5F101GEDNA#W0, R5F101GFDNA#W0, R5F101GGDNA#W0, R5F101GHDNA#W0, R5F101GJDNA#W0, R5F101GKDNA#W0, R5F101GLDNA#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(7/12)

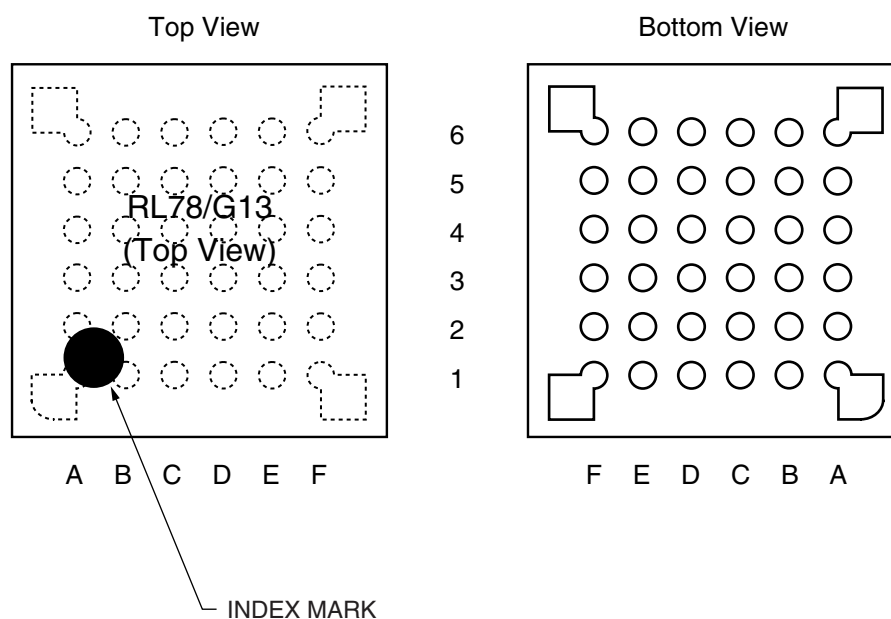
Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
52 pins	52-pin plastic LQFP (10 × 10 mm, 0.65 mm pitch)	Mounted	A D G	R5F100JCAFA#V0, R5F100JDAFA#V0, R5F100JEAFA#V0, R5F100JFAFA#V0, R5F100JGAFA#V0, R5F100JHAFA#V0, R5F100JJAFA#V0, R5F100JKAFa#V0, R5F100JLAFA#V0 R5F100JCAFA#X0, R5F100JDAFA#X0, R5F100JEAFA#X0, R5F100JFAFA#X0, R5F100JGAFA#X0, R5F100JHAFA#X0, R5F100JJAFA#X0, R5F100JKAFa#X0, R5F100JLAFA#X0 R5F100JCDFA#V0, R5F100JDDFA#V0, R5F100JEDFA#V0, R5F100JFDFA#V0, R5F100JGDFA#V0, R5F100JHDFA#V0, R5F100JJDFA#V0, R5F100JKDFA#V0, R5F100JLDFA#V0 R5F100JCDFA#X0, R5F100JDDFA#X0, R5F100JEDFA#X0, R5F100JFDFA#X0, R5F100JGDFA#X0, R5F100JHDFA#X0, R5F100JJDFA#X0, R5F100JKDFA#X0, R5F100JLDFA#X0 R5F100JCGFA#V0, R5F100JDGFA#V0, R5F100JEGFA#V0, R5F100JFGFA#V0, R5F100JGGFA#V0, R5F100JHGFA#V0, R5F100JJGFA#V0 R5F100JCGFA#X0, R5F100JDGFA#X0, R5F100JEGFA#X0, R5F100JFGFA#X0, R5F100JGGFA#X0, R5F100JHGFA#X0, R5F100JJGFA#X0
		Not mounted	A D	R5F101JCAFA#V0, R5F101JDAFA#V0, R5F101JEAFA#V0, R5F101JFAFA#V0, R5F101JGAFA#V0, R5F101JHAFA#V0, R5F101JJAFA#V0, R5F101JKAFa#V0, R5F101JLAFA#V0 R5F101JCAFA#X0, R5F101JDAFA#X0, R5F101JEAFA#X0, R5F101JFAFA#X0, R5F101JGAFA#X0, R5F101JHAFA#X0, R5F101JJAFA#X0, R5F101JKAFa#X0, R5F101JLAFA#X0 R5F101JCDFA#V0, R5F101JDDFA#V0, R5F101JEDFA#V0, R5F101JFDFA#V0, R5F101JGDFA#V0, R5F101JHDFA#V0, R5F101JJDFA#V0, R5F101JKDFA#V0, R5F101JLDFA#V0 R5F101JCDFA#X0, R5F101JDDFA#X0, R5F101JEDFA#X0, R5F101JFDFA#X0, R5F101JGDFA#X0, R5F101JHDFA#X0, R5F101JJDFA#X0, R5F101JKDFA#X0, R5F101JLDFA#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.6 36-pin products

- 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



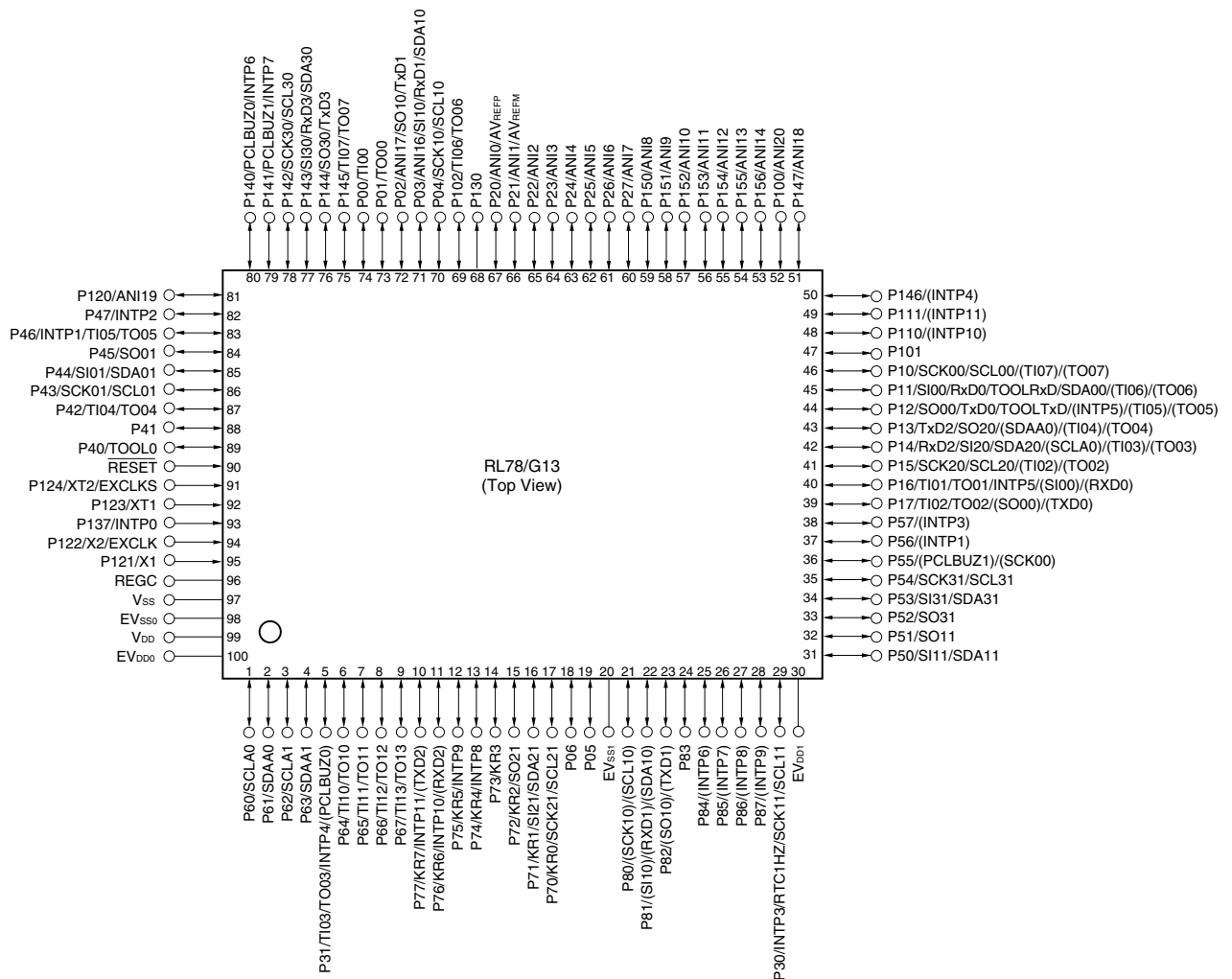
	A	B	C	D	E	F	
6	P60/SCLA0	V _{DD}	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	6
5	P62	P61/SDAA0	V _{SS}	REGC	RESET	P120/ANI19	5
4	P72/SO21	P71/SI21/ SDA21	P14/RxD2/SI20/ SDA20/(SCLA0)/ (TI03)/(TO03)	P31/TI03/TO03/ INTP4/ PCLBUZ0	P00/TI00/TxD1	P01/TO00/RxD1	4
3	P50/INTP1/ SI11/SDA11	P70/SCK21/ SCL21	P15/PCLBUZ1/ SCK20/SCL20/ (TI02)/(TO02)	P22/ANI2	P20/ANI0/ AV _{REFP}	P21/ANI1/ AV _{REFM}	3
2	P30/INTP3/ SCK11/SCL11	P16/TI01/TO01/ INTP5/(RxD0)	P12/SO00/ TxD0/TOOLTxD/ (TI05)/(TO05)	P11/SI00/RxD0/ TOOLRxD/ SDA00/(TI06)/ (TO06)	P24/ANI4	P23/ANI3	2
1	P51/INTP2/ SO11	P17/TI02/TO02/ (TxD0)	P13/TxD2/ SO20/(SDAA0)/ (TI04)/(TO04)	P10/SCK00/ SCL00/(TI07)/ (TO07)	P147/ANI18	P25/ANI5	1
	A	B	C	D	E	F	

Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

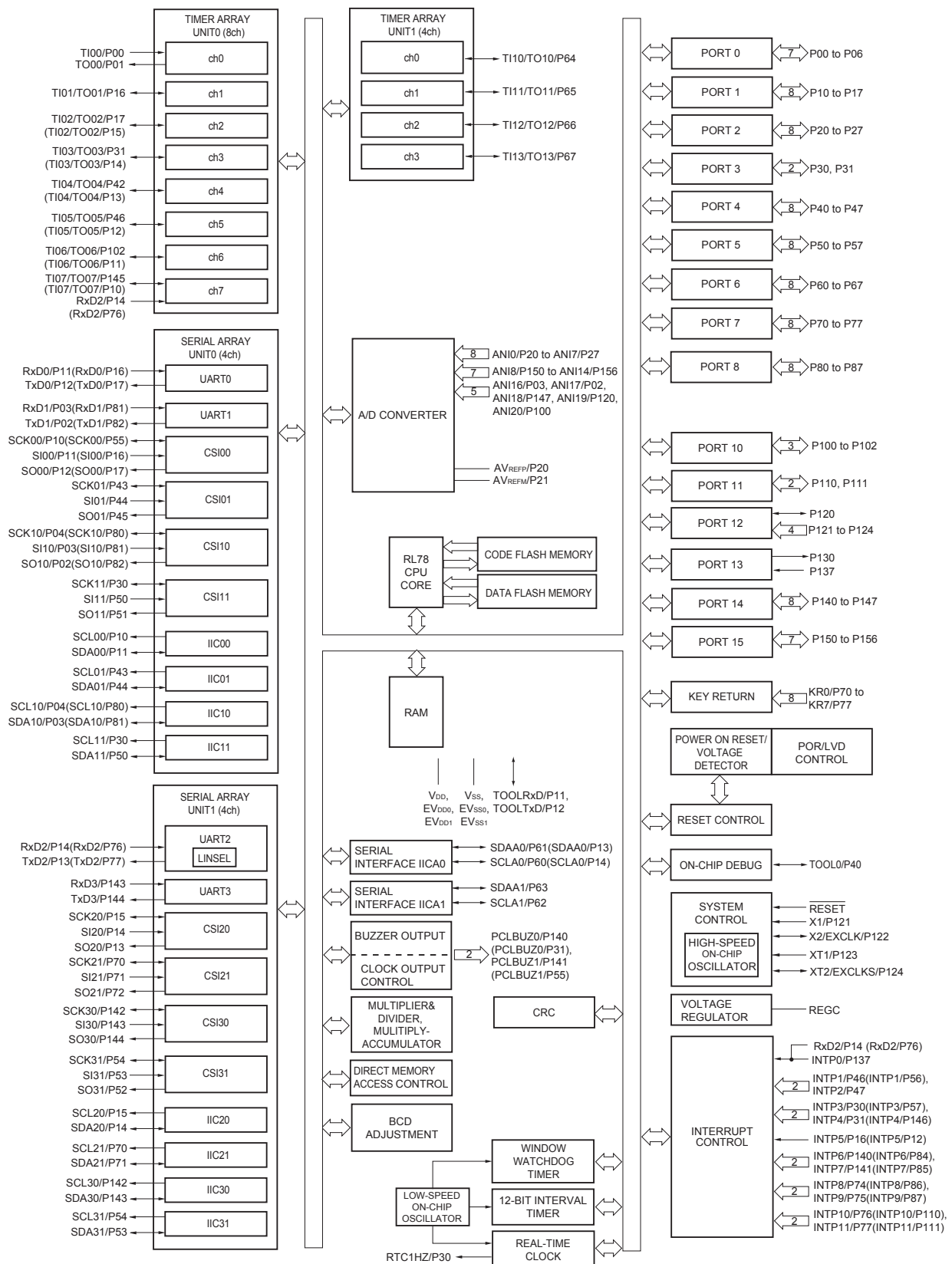
- 100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)



- Cautions**
1. Make EV_{SS0}, EV_{SS1} pins the same potential as V_{SS} pin.
 2. Make V_{DD} pin the potential that is higher than EV_{DD0}, EV_{DD1} pins (EV_{DD0} = EV_{DD1}).
 3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF).

- Remarks**
1. For pin identification, see 1.4 Pin Identification.
 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the V_{SS}, EV_{SS0} and EV_{SS1} pins to separate ground lines.
 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.13 100-pin products

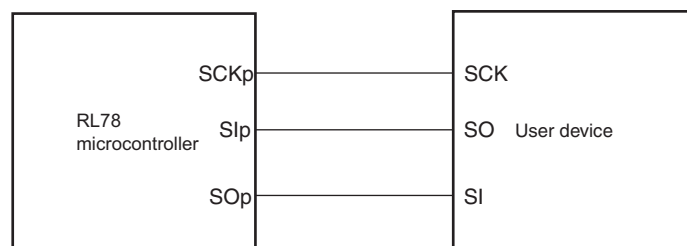
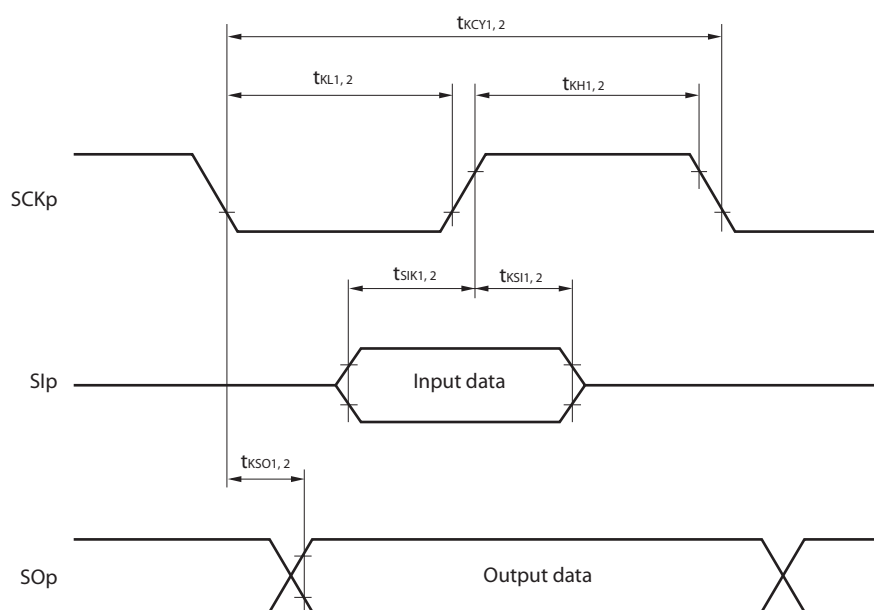
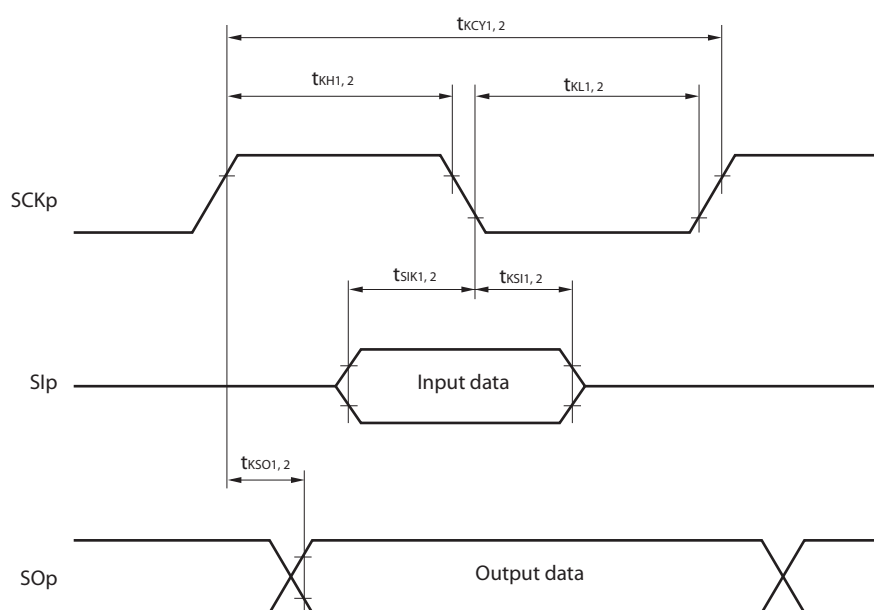


Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products**(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (1/2)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating mode	HS (high-speed main) mode Note 5	f _{IH} = 32 MHz Note 3	Basic operation	V _{DD} = 5.0 V		2.3		mA
						V _{DD} = 3.0 V		2.3		mA
					Normal operation	V _{DD} = 5.0 V		5.2	8.5	mA
						V _{DD} = 3.0 V		5.2	8.5	mA
				f _{IH} = 24 MHz Note 3	Normal operation	V _{DD} = 5.0 V		4.1	6.6	mA
						V _{DD} = 3.0 V		4.1	6.6	mA
				f _{IH} = 16 MHz Note 3	Normal operation	V _{DD} = 5.0 V		3.0	4.7	mA
						V _{DD} = 3.0 V		3.0	4.7	mA
			LS (low-speed main) mode Note 5	f _{IH} = 8 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.3	2.1	mA
						V _{DD} = 2.0 V		1.3	2.1	mA
			LV (low-voltage main) mode Note 5	f _{IH} = 4 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.3	1.8	mA
						V _{DD} = 2.0 V		1.3	1.8	mA
			HS (high-speed main) mode Note 5	f _{MX} = 20 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		3.4	5.5	mA
						Resonator connection		3.6	5.7	mA
				f _{MX} = 20 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		3.4	5.5	mA
						Resonator connection		3.6	5.7	mA
				f _{MX} = 10 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		2.1	3.2	mA
						Resonator connection		2.1	3.2	mA
				f _{MX} = 10 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		2.1	3.2	mA
						Resonator connection		2.1	3.2	mA
			LS (low-speed main) mode Note 5	f _{MX} = 8 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		1.2	2.0	mA
						Resonator connection		1.2	2.0	mA
				f _{MX} = 8 MHz Note 2, V _{DD} = 2.0 V	Normal operation	Square wave input		1.2	2.0	mA
						Resonator connection		1.2	2.0	mA
			Subsystem clock operation	f _{SUB} = 32.768 kHz Note 4 T _A = -40°C	Normal operation	Square wave input		4.8	5.9	μA
						Resonator connection		4.9	6.0	μA
				f _{SUB} = 32.768 kHz Note 4 T _A = +25°C	Normal operation	Square wave input		4.9	5.9	μA
						Resonator connection		5.0	6.0	μA
				f _{SUB} = 32.768 kHz Note 4 T _A = +50°C	Normal operation	Square wave input		5.0	7.6	μA
						Resonator connection		5.1	7.7	μA
				f _{SUB} = 32.768 kHz Note 4 T _A = +70°C	Normal operation	Square wave input		5.2	9.3	μA
						Resonator connection		5.3	9.4	μA
				f _{SUB} = 32.768 kHz Note 4 T _A = +85°C	Normal operation	Square wave input		5.7	13.3	μA
						Resonator connection		5.8	13.4	μA

(Notes and Remarks are listed on the next page.)

CSI mode connection diagram (during communication at same potential)**CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)****CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)**

- Remarks**
1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)
 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)
(3/3)

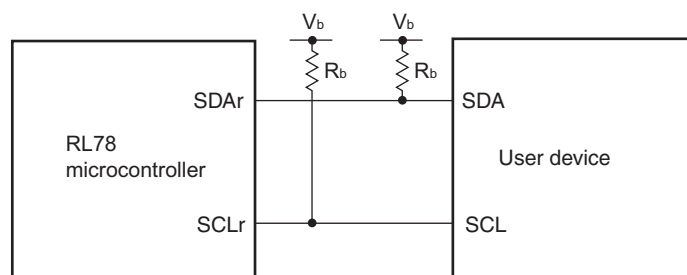
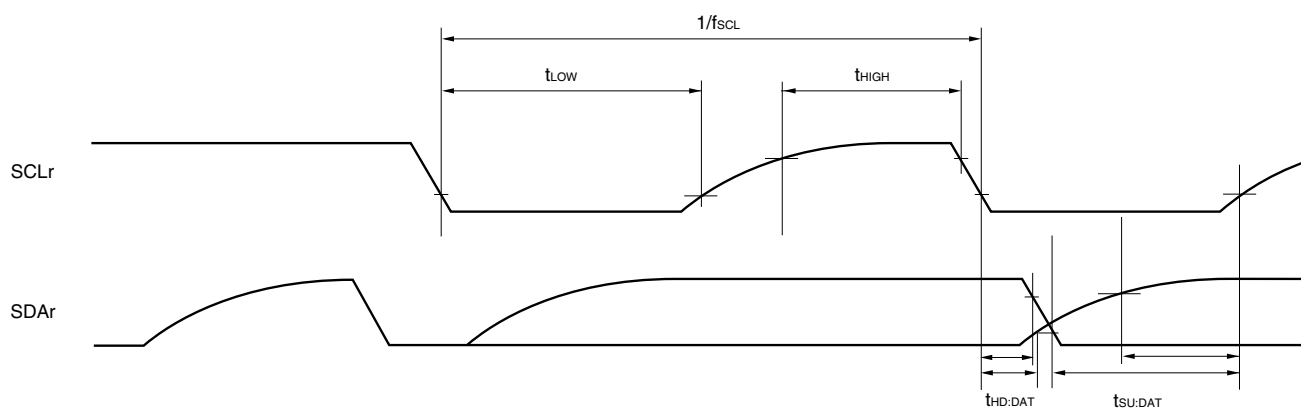
(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Slp setup time (to SCKp↓) ^{Note 1}	t _{SIK1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	44		110		110		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	44		110		110		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ	110		110		110		ns
Slp hold time (from SCKp↓) ^{Note 1}	t _{KSH1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	19		19		19		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↑ to SOp output ^{Note 1}	t _{KSO1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ		25		25		25	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		25		25		25	ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ		25		25		25	ns

- Notes**
1. When DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.
 2. Use it with EV_{DD0} ≥ V_b.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)**Simplified I²C mode serial transfer timing (during communication at different potential)**

- Remarks**
1. $R_b[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance, $V_b[V]$: Communication line voltage
 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))

LVD Detection Voltage of Interrupt & Reset Mode(T_A = -40 to +85°C, V_{PDR} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	VLVDA0	V _{POC2} , V _{POC1} , V _{POC0} = 0, 0, 0, falling reset voltage		1.60	1.63	1.66	V
	VLVDA1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
			Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
			Falling interrupt voltage	1.80	1.84	1.87	V
	VLVDA3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDB0	V _{POC2} , V _{POC1} , V _{POC0} = 0, 0, 1, falling reset voltage		1.80	1.84	1.87	V
	VLVDB1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
			Falling interrupt voltage	1.90	1.94	1.98	V
	VLVDB2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
			Falling interrupt voltage	2.00	2.04	2.08	V
	VLVDB3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
			Falling interrupt voltage	3.00	3.06	3.12	V
	VLVDC0	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 0, falling reset voltage		2.40	2.45	2.50	V
	VLVDC1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
			Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
			Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
			Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 1, falling reset voltage		2.70	2.75	2.81	V
	VLVDD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
			Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
			Falling interrupt voltage	3.90	3.98	4.06	V

- Notes**
1. Total current flowing into V_{DD} , EV_{DD0} , and EV_{DD1} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} , and EV_{DD1} , or V_{SS} , EV_{SS0} , and EV_{SS1} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 4. When high-speed system clock and subsystem clock are stopped.
 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$

8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.

- Remarks**
1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH} : High-speed on-chip oscillator clock frequency
 3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

3.4 AC Characteristics

(T_A = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T _{cy}	Main system clock (f _{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		Subsystem clock (f _{SUB}) operation		2.4 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
External system clock frequency	f _{EX}	2.7 V ≤ V _{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V _{DD} < 2.7 V			1.0		16.0	MHz
	f _{EXS}				32		35	kHz
External system clock input high-level width, low-level width	t _{EXH} , t _{EXL}	2.7 V ≤ V _{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V _{DD} < 2.7 V			30			ns
	t _{EXHS} , t _{EXLS}				13.7			μs
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	t _{TIH} , t _{TIL}				1/f _{MCK} +10			ns ^{Note}
TO00 to TO07, TO10 to TO17 output frequency	f _{TO}	HS (high-speed main) mode	4.0 V ≤ EV _{DD0} ≤ 5.5 V				16	MHz
			2.7 V ≤ EV _{DD0} < 4.0 V				8	MHz
			2.4 V ≤ EV _{DD0} < 2.7 V				4	MHz
PCLBUZ0, PCLBUZ1 output frequency	f _{PCL}	HS (high-speed main) mode	4.0 V ≤ EV _{DD0} ≤ 5.5 V				16	MHz
			2.7 V ≤ EV _{DD0} < 4.0 V				8	MHz
			2.4 V ≤ EV _{DD0} < 2.7 V				4	MHz
Interrupt input high-level width, low-level width	t _{INTH} , t _{INTL}	INTP0	2.4 V ≤ V _{DD} ≤ 5.5 V		1			μs
		INTP1 to INTP11	2.4 V ≤ EV _{DD0} ≤ 5.5 V		1			μs
Key interrupt input low-level width	t _{KR}	KR0 to KR7	2.4 V ≤ EV _{DD0} ≤ 5.5 V		250			ns
RESET low-level width	t _{RSL}				10			μs

Note The following conditions are required for low voltage interface when $\text{EV}_{\text{DD}0} < \text{V}_{\text{DD}}$
 $2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 2.7\text{ V}$: MIN. 125 ns

Remark f_{MCK}: Timer array unit operation clock frequency
 (Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).
 m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate		Transmission	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V		
			Theoretical value of the maximum transfer rate C _b = 50 pF, R _b = 1.4 kΩ, V _b = 2.7 V		
				Note 1	bps
				2.6 ^{Note 2}	Mbps
			2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V		
			Theoretical value of the maximum transfer rate C _b = 50 pF, R _b = 2.7 kΩ, V _b = 2.3 V		
					Note 3
					1.2 ^{Note 4}
					Mbps
			2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V		
			Theoretical value of the maximum transfer rate C _b = 50 pF, R _b = 5.5 kΩ, V _b = 1.6 V		
					Note 5
					0.43 ^{Note 6}

Notes 1. The smaller maximum transfer rate derived by using f_{MCK}/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD0} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- The smaller maximum transfer rate derived by using f_{MCK}/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD0} < 4.0 V and 2.4 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

5. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $2.4\text{ V} \leq E_{VDD0} < 3.3\text{ V}$ and $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

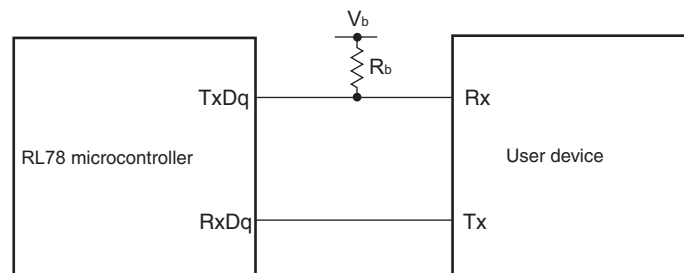
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

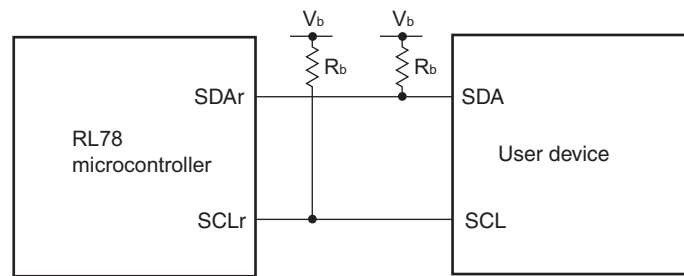
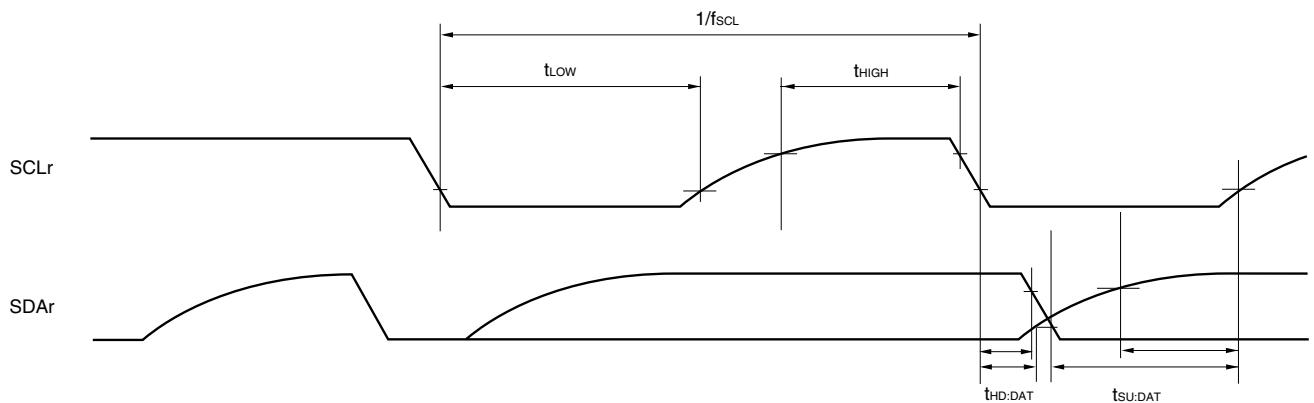
* This value is the theoretical value of the relative difference between the transmission and reception sides.

6. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ E_{VDD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



Simplified I²C mode connection diagram (during communication at different potential)**Simplified I²C mode serial transfer timing (during communication at different potential)**

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

- Remarks**
1. $R_b[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance, $V_b[V]$: Communication line voltage
 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))

3.5.2 Serial interface IICA

(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode				Unit
			Standard Mode		Fast Mode		
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f _{SCL}	Fast mode: f _{CLK} ≥ 3.5 MHz	–	–	0	400	kHz
		Standard mode: f _{CLK} ≥ 1 MHz	0	100	–	–	kHz
Setup time of restart condition	t _{SU:STA}		4.7		0.6		μs
Hold time ^{Note 1}	t _{HD:STA}		4.0		0.6		μs
Hold time when SCLA0 = “L”	t _{LOW}		4.7		1.3		μs
Hold time when SCLA0 = “H”	t _{HIGH}		4.0		0.6		μs
Data setup time (reception)	t _{SU:DAT}		250		100		ns
Data hold time (transmission) ^{Note 2}	t _{HD:DAT}		0	3.45	0	0.9	μs
Setup time of stop condition	t _{SU:STO}		4.0		0.6		μs
Bus-free time	t _{BUF}		4.7		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

<R> 2. The maximum value (MAX.) of tHD:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

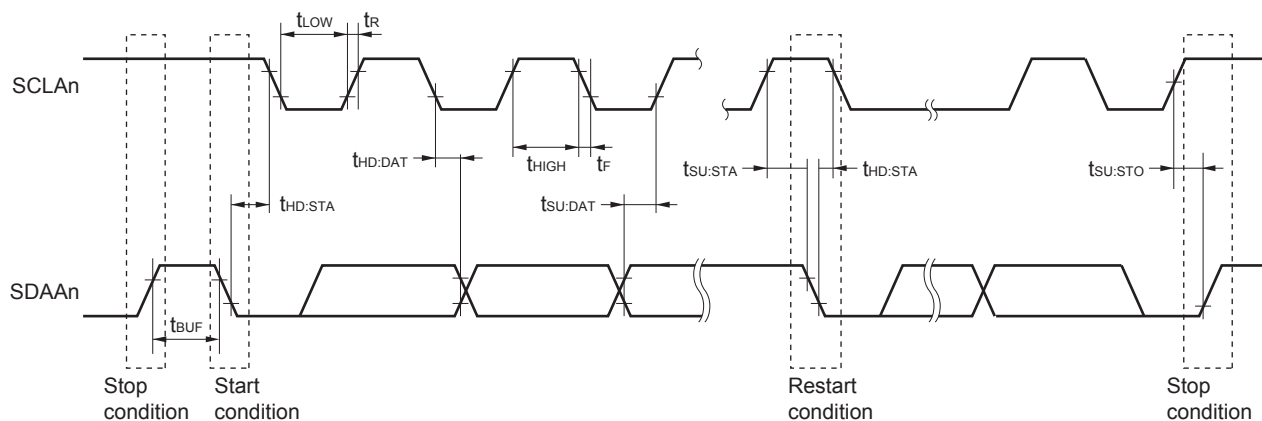
Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: Cb = 400 pF, Rb = 2.7 kΩ

Fast mode: Cb = 320 pF, Rb = 1.1 kΩ

IICA serial transfer timing

**Remark** n = 0, 1

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (-) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (-) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (-) = AV_{REFM}
ANI0 to ANI14	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI26	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1).		—

(1) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (-) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$	1.2	± 3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2 to ANI14	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
Zero-scale error ^{Notes 1, 2}	E_{ZS}	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.25	%FSR
Full-scale error ^{Notes 1, 2}	E_{FS}	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 2.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 1.5	LSB
Analog input voltage	V_{AIN}	ANI2 to ANI14	0		AV_{REFP}	V
		Internal reference voltage output ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)	V_{BGR} ^{Note 4}			V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)	V_{TMPS25} ^{Note 4}			V

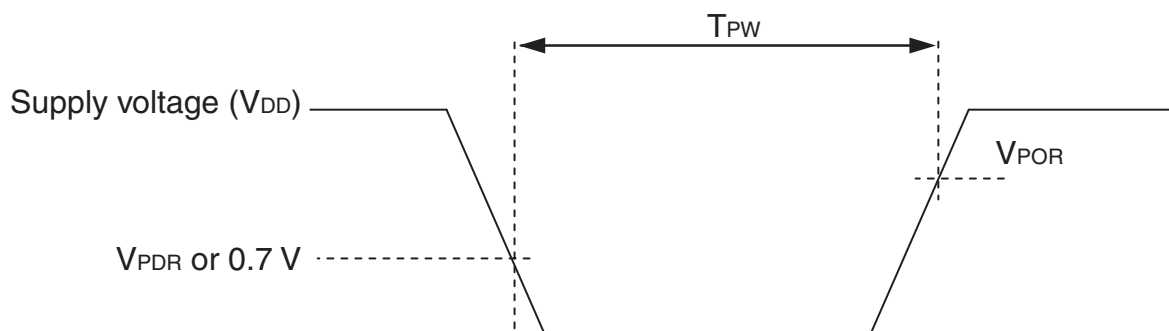
(Notes are listed on the next page.)

3.6.3 POR circuit characteristics

 $(T_A = -40$ to $+105^\circ\text{C}$, $V_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.45	1.51	1.57	V
	V_{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width	T_{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR} . This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



NOTES FOR CMOS DEVICES

- (1) **VOLTAGE APPLICATION WAVEFORM AT INPUT PIN:** Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (MAX) and V_{IH} (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (MAX) and V_{IH} (MIN).
- (2) **HANDLING OF UNUSED INPUT PINS:** Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) **PRECAUTION AGAINST ESD:** A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) **STATUS BEFORE INITIALIZATION:** Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) **POWER ON/OFF SEQUENCE:** In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) **INPUT OF SIGNAL DURING POWER OFF STATE :** Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.